

## Inverter Grade Thyristors (Stud Version), 85 A



### FEATURES

- Center amplifying gate
- High surge current capability
- Low thermal impedance
- High speed performance
- Compression bonding
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT

### PRODUCT SUMMARY

Package	TO-209AC (TO-94)
Diode variation	Single SCR
$I_{T(AV)}$	85 A
$V_{DRM}/V_{RRM}$	400 V to 1200 V
$V_{TM}$	2.15 V
$I_{TSM}$ at 50 Hz	2450 A
$I_{TSM}$ at 60 Hz	2560 A
$I_{GT}$	200 mA
$T_C/T_{hs}$	85 °C

### TYPICAL APPLICATIONS

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

### MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		85	A
	$T_C$	85	°C
$I_{T(RMS)}$		135	A
$I_{TSM}$	50 Hz	2450	A
	60 Hz	2560	A
$I^2t$	50 Hz	30	kA <sup>2</sup> s
	60 Hz	27	
$V_{DRM}/V_{RRM}$		400 to 1200	V
$t_q$	Range	10 to 20	µs
$T_J$		-40 to 125	°C

### ELECTRICAL SPECIFICATIONS

#### VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	$V_{DRM}/V_{RRM}$ : MAXIMUM REPETITIVE PEAK VOLTAGE V	$V_{RSM}$ : MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAX. AT $T_J = T_J$ MAX. mA
VS-ST083S	04	400	500	30
	08	800	900	
	10	1000	1100	
	12	1200	1300	



CURRENT CARRYING CAPABILITY							
FREQUENCY							UNITS
50 Hz	210	120	330	270	2540	1930	A
400 Hz	200	120	350	210	1190	810	
1000 Hz	150	80	320	190	630	400	
2500 Hz	70	25	220	85	250	100	
Recovery voltage $V_r$	50	50	50	50	50	50	V
Voltage before turn-on $V_d$	$V_{DRM}$		$V_{DRM}$		$V_{DRM}$		
Rise of on-state current $di/dt$	50	50	-	-	-	-	A/μs
Case temperature	60	85	60	85	60	85	°C
Equivalent values for RC circuit	22/0.15		22/0.15		22/0.15		W/μF

ON-STATE CONDUCTION					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		85	A
				85	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 77 °C case temperature		135	A
Maximum peak, one half cycle, non-repetitive surge current	$I_{TSM}$	t = 10 ms	No voltage reappplied	2450	
		t = 8.3 ms	No voltage reappplied	2560	
		t = 10 ms	100 % $V_{RRM}$ reappplied	2060	
		t = 8.3 ms	100 % $V_{RRM}$ reappplied	2160	
Maximum $I^2t$ for fusing	$I^2t$	t = 10 ms	No voltage reappplied	30	kA <sup>2</sup> s
		t = 8.3 ms	No voltage reappplied	27	
		t = 10 ms	100 % $V_{RRM}$ reappplied	21	
		t = 8.3 ms	100 % $V_{RRM}$ reappplied	19	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reappplied		300	kA <sup>2</sup> /√s
Maximum peak on-state voltage	$V_{TM}$	$I_{TM} = 300$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse		2.15	V
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		1.46	
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		1.52	
Low level value of forward slope resistance	$r_{t1}$	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		2.32	
High level value of forward slope resistance	$r_{t2}$	$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum		2.34	mΩ
Maximum holding current	$I_H$	$T_J = 25$ °C, $I_T > 30$ A		600	mA
Typical latching current	$I_L$	$T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ Ω, $I_G = 1$ A		1000	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			MIN.	MAX.	
Maximum non-repetitive rate of rise of turned on current	$di/dt$	$T_J = T_J$ max., $V_{DRM} = \text{Rated } V_{DRM}$ , $I_{TM} = 2 \times di/dt$	1000		A/μs
Typical delay time	$t_d$	$T_J = 25$ °C, $V_{DM} = \text{Rated } V_{DM}$ , $I_{TM} = 50$ A DC, $t_p = 1$ μs Resistive load, gate pulse: 10 V, 5 Ω source	0.80		μs
Maximum turn-off time	$t_q$	$T_J = T_J$ maximum, $I_{TM} = 100$ A, commutating $di/dt = 10$ A/μs $V_R = 50$ V, $t_p = 200$ μs, $dV/dt = 200$ V/μs	10	20	



BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ , higher value available on request	500	V/ $\mu$ s
Maximum peak reverse and off-state leakage current	$I_{RRM}$ , $I_{DRM}$	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	30	mA

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	40	W
Maximum average gate power	$P_{G(AV)}$		5	
Maximum peak positive gate current	$I_{GM}$	$T_J = T_J$ maximum, $t_p \leq 5$ ms	5	A
Maximum peak positive gate voltage	$+V_{GM}$		20	V
Maximum peak negative gate voltage	$-V_{GM}$		5	
Maximum DC gate current required to trigger	$I_{GT}$	$T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ $\Omega$	200	mA
Maximum DC gate voltage required to trigger	$V_{GT}$		3	V
Maximum DC gate current not to trigger	$I_{GD}$	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	20	mA
Maximum DC gate voltage not to trigger	$V_{GD}$		0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	$T_J$		-40 to 125	°C
Maximum storage temperature range	$T_{Stg}$		-40 to 150	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	0.195	K/W
Maximum thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, smooth, flat and greased	0.08	
Mounting torque, $\pm 10$ %		Non-lubricated threads	15.5 (137)	N · m (lbf · in)
		Lubricated threads	14 (120)	
Approximate weight			130	g
Case style		See dimensions - link at the end of datasheet	TO-209AC (TO-94)	

$\Delta R_{thJC}$ CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.034	0.025	$T_J = T_J$ maximum	K/W
120°	0.041	0.042		
90°	0.052	0.056		
60°	0.076	0.079		
30°	0.126	0.127		

**Note**

- The table above shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

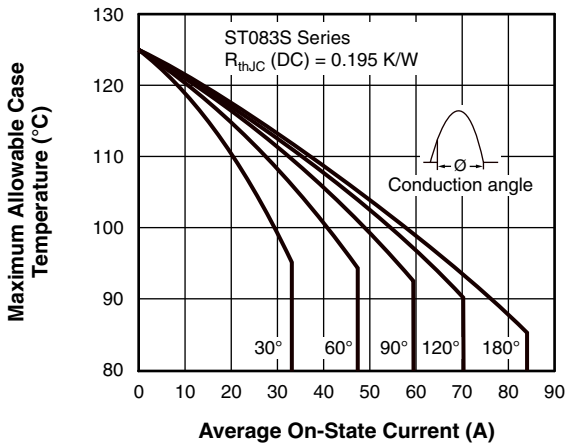


Fig. 1 - Current Ratings Characteristics

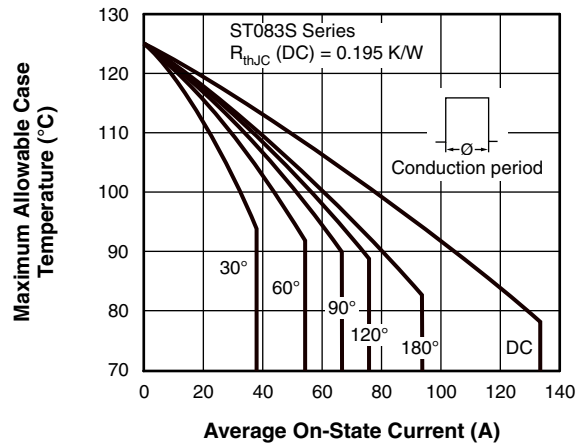


Fig. 2 - Current Ratings Characteristics

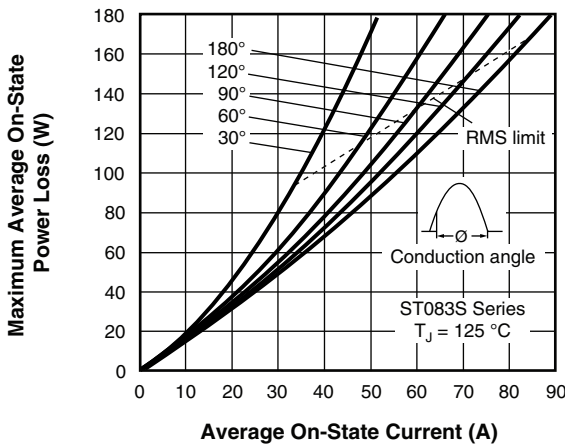


Fig. 3 - On-State Power Loss Characteristics

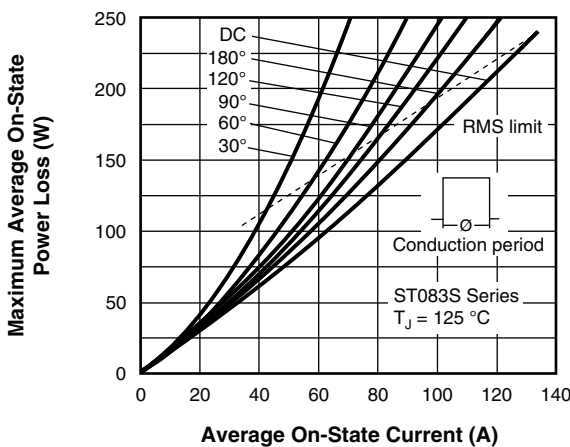
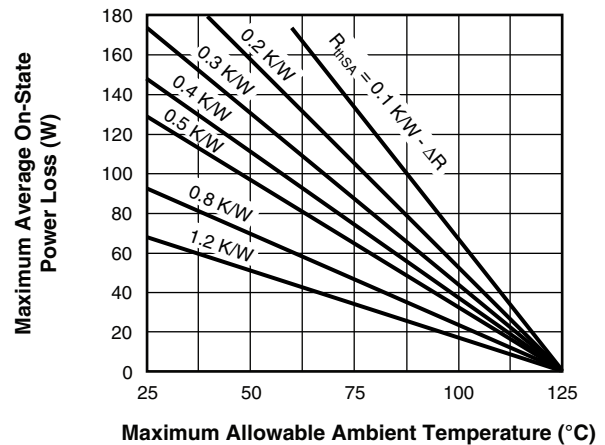
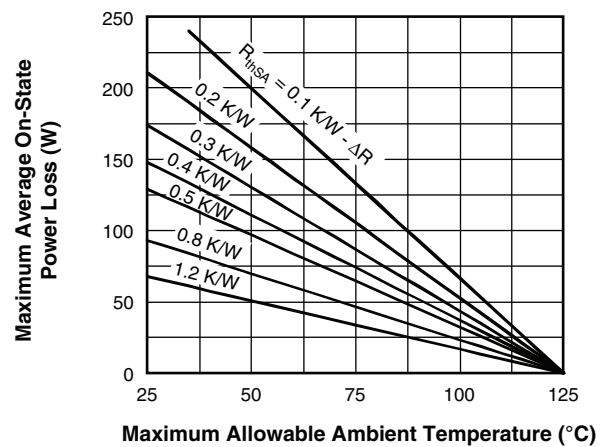


Fig. 4 - On-State Power Loss Characteristics



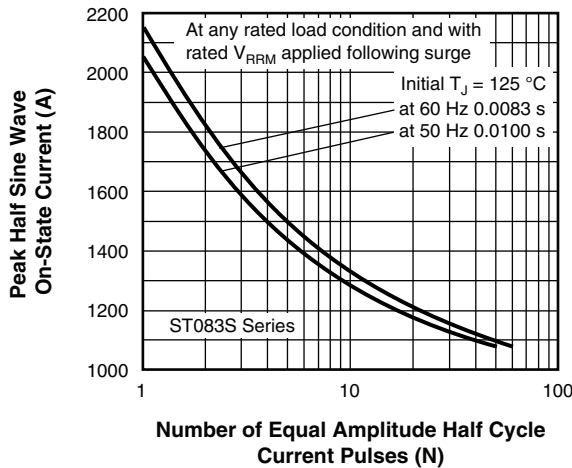


Fig. 5 - Maximum Non-Repetitive Surge Current

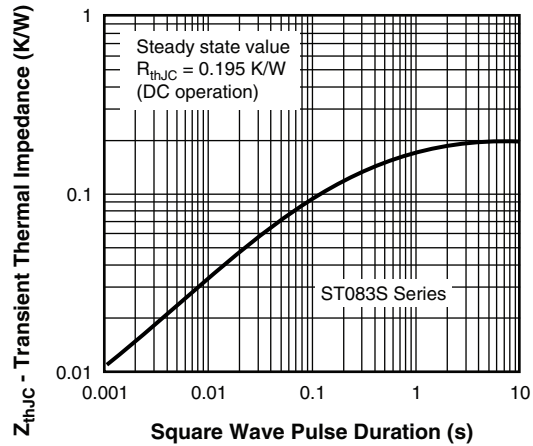


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristic

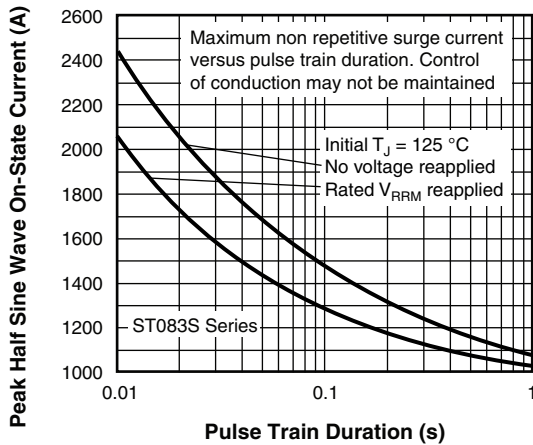


Fig. 6 - Maximum Non-Repetitive Surge Current

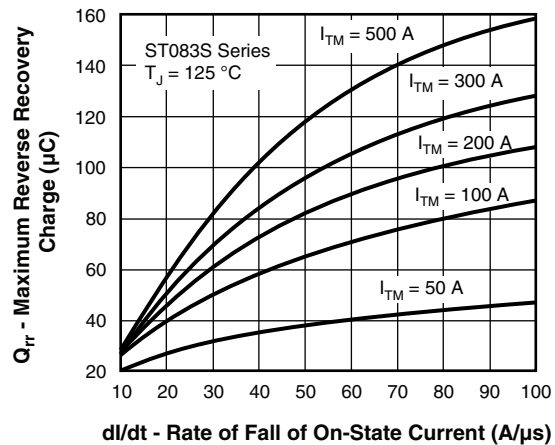


Fig. 9 - Reverse Recovered Charge Characteristics

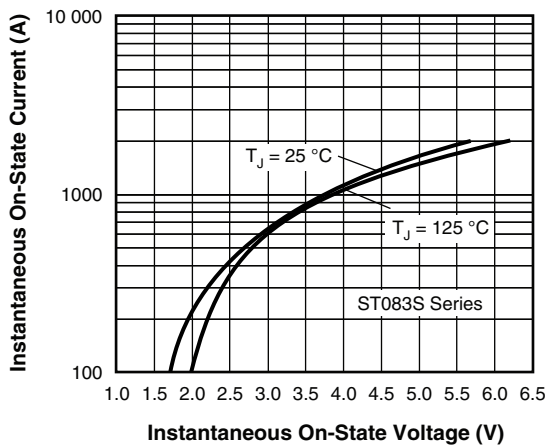


Fig. 7 - On-State Voltage Drop Characteristics

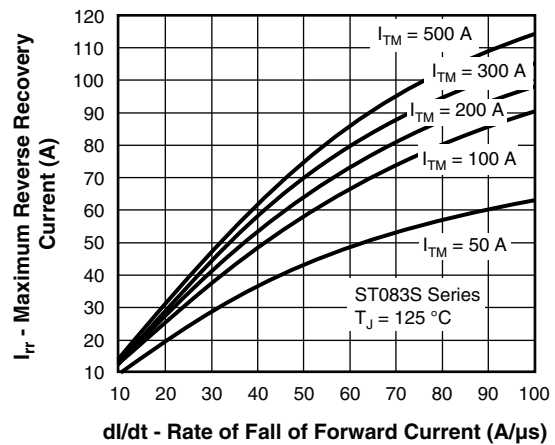


Fig. 10 - Reverse Recovery Current Characteristics

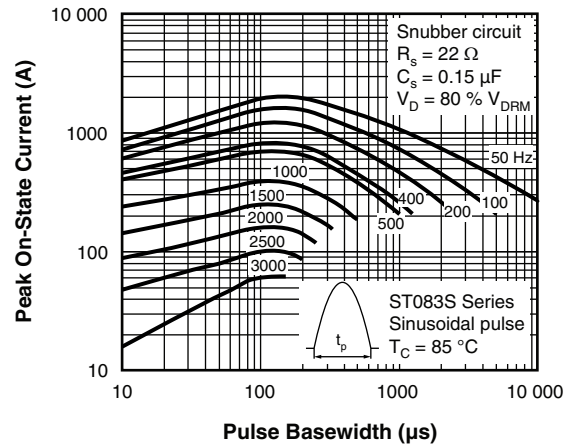
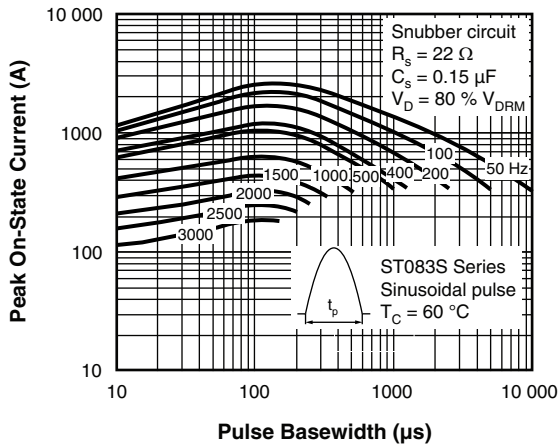


Fig. 11 - Frequency Characteristics

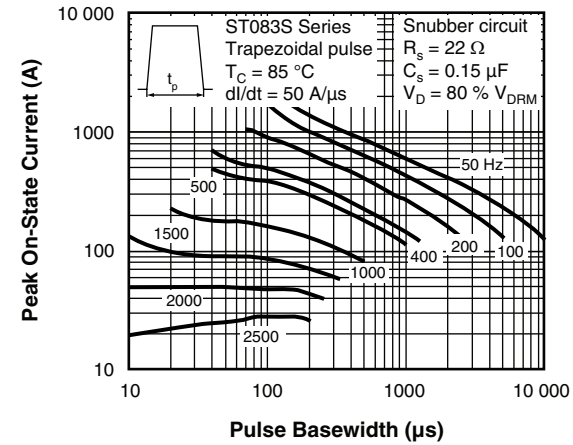
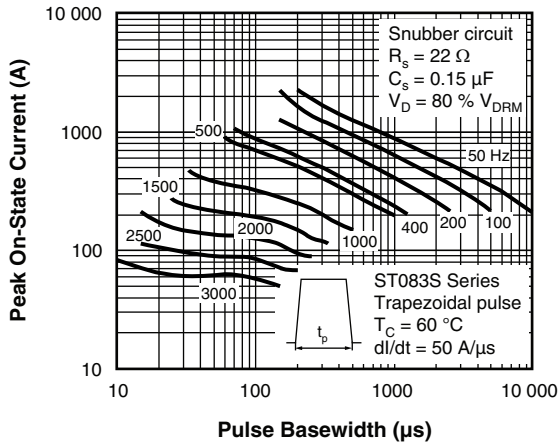


Fig. 12 - Frequency Characteristics

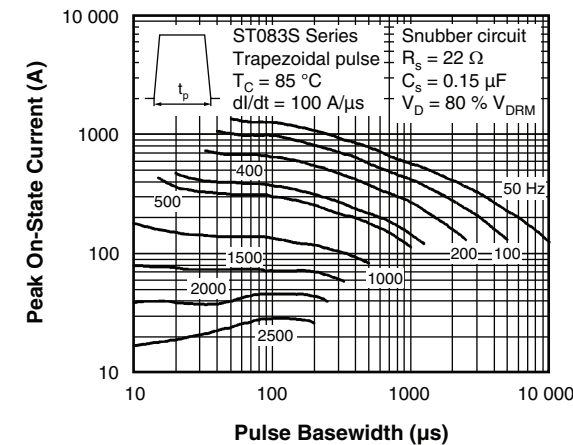
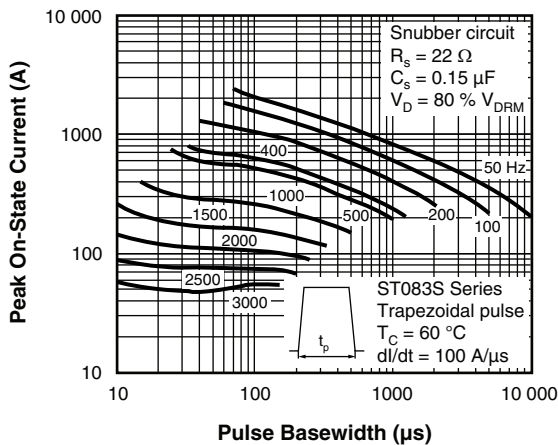


Fig. 13 - Frequency Characteristics

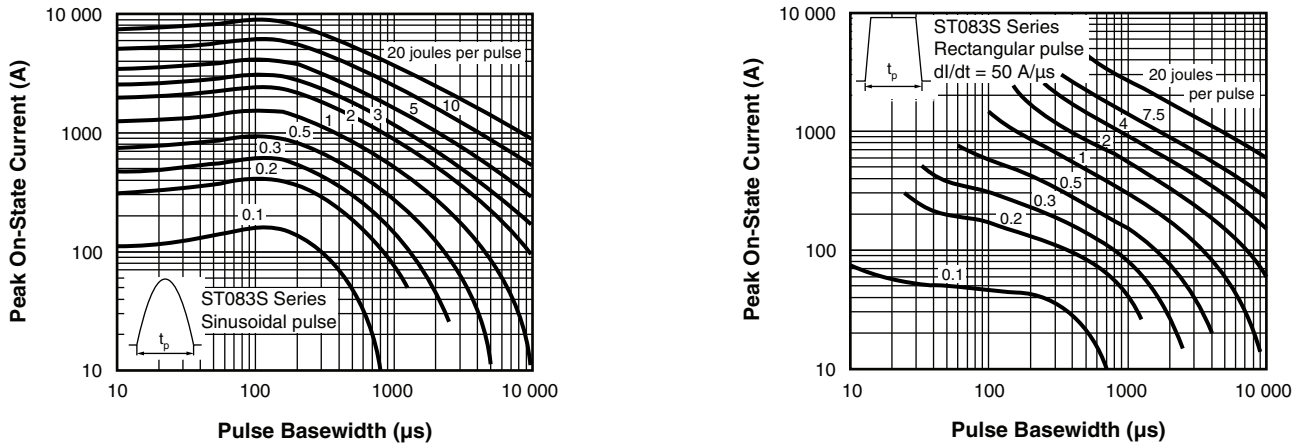


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

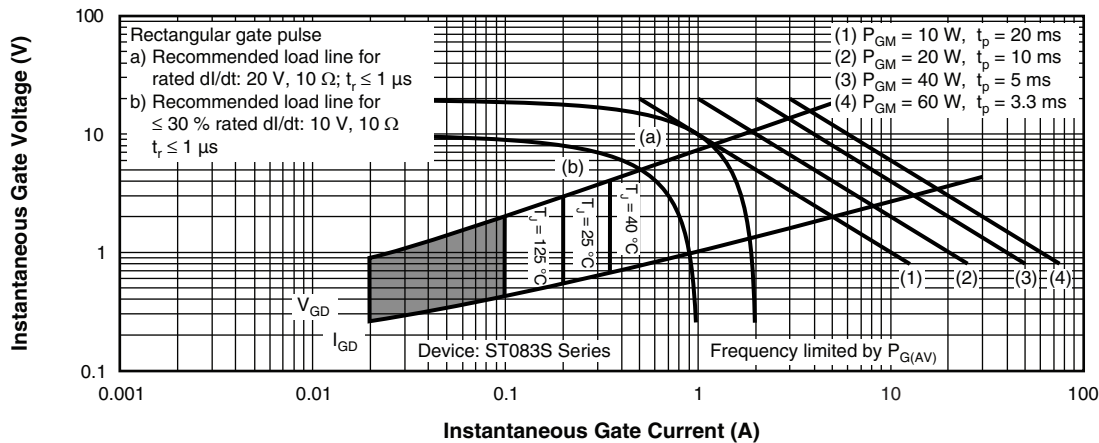
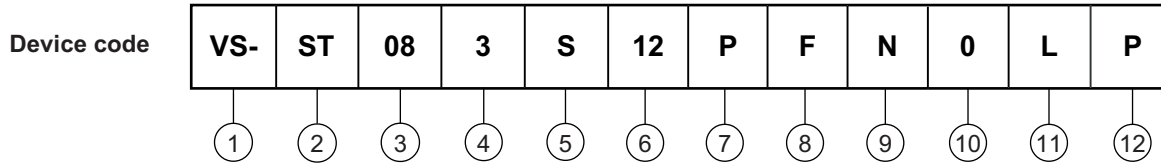


Fig. 15 - Gate Characteristics



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - Thyristor
- 3** - Essential part number
- 4** - 3 = Fast turn-off
- 5** - S = Compression bonding stud
- 6** - Voltage code x 100 =  $V_{RRM}$  (see Voltage Ratings table)
- 7** -
  - P = Stud base 1/2"-20UNF-2A threads
  - M = Metric M12, contact factory for availability
- 8** - Reapplied dV/dt code (for  $t_q$  test condition)
- 9** -  $t_q$  code
- 10** -
  - 0 = Eyelet terminals (gate and aux. cathode leads)
  - 1 = Fast-on terminals (gate and aux. cathode leads)
  - 2 = Flag terminals (gate and aux. cathode leads)
- 11** - Critical dV/dt:
  - None = 500 V/ $\mu$ s (standard value)
  - L = 1000 V/ $\mu$ s (special selection)
- 12** - None = Standard production; P = Lead (Pb)-free

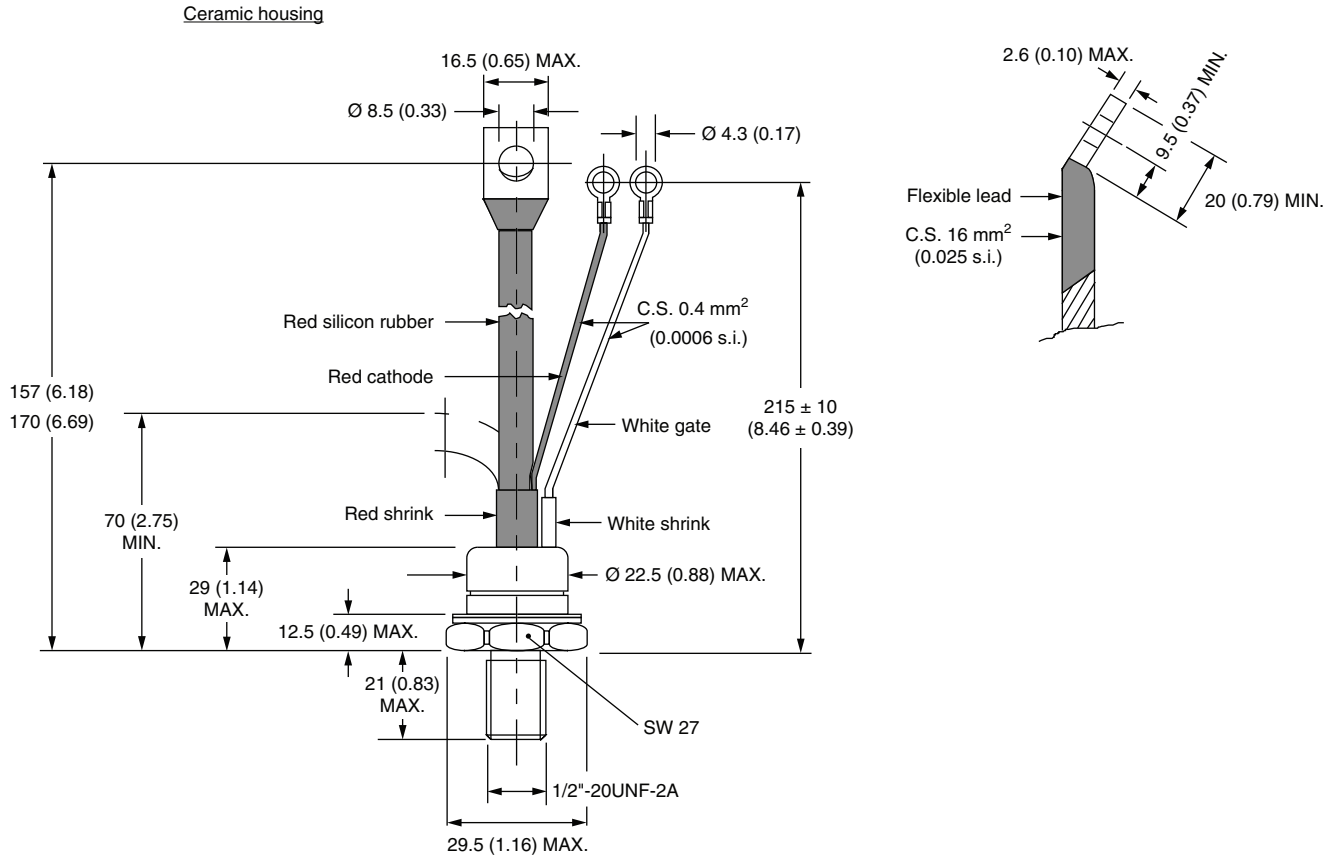
dV/dt - $t_q$ combinations available		
	dV/dt (V/ $\mu$ s)	200
$t_q$ ( $\mu$ s) up to 800V	10	FN
	20	FK
$t_q$ ( $\mu$ s) only for 1000/1200 V	20	FK

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95003">www.vishay.com/doc?95003</a>



## TO-209AC (TO-94) for ST083S and ST103S Series

**DIMENSIONS** in millimeters (inches)





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